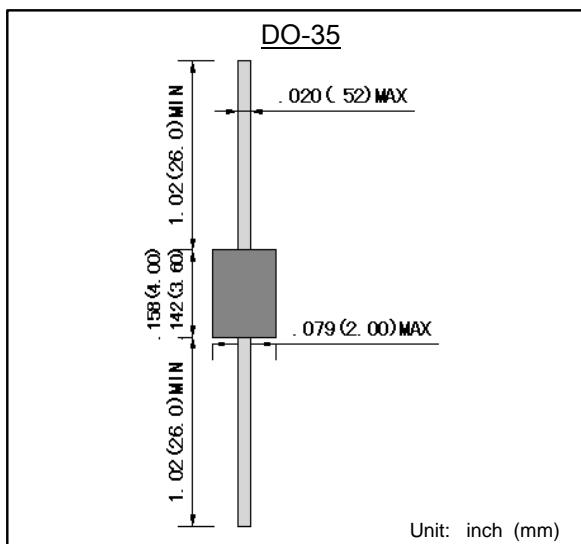


玻封双向触发二极管
击穿电压 28 ~ 36 V

Glass Bi-directional Trigger Diode
Breakover Voltage 28 ~ 36V



特征 Features

- 高可靠性玻璃钝化芯片 High reliability glass passivation chip
- 击穿电流低 Low breakover current
- 高信赖性 High reliability
- 高温焊接保证 High temperature soldering guaranteed:
260°C/10 秒 260°C/10seconds
- 引线镀层皆符合RoHS标准 Lead and body according with RoHS standard

机械数据 Mechanical Data

- 封装: DO-35 玻璃封装 Case: DO-35 Glass Case
- 引脚 : 纯锡 , 无铅 Lead: Pure tin, lead free

最大值和特性 TA = 25°C 除非另有规定。

Maximum Ratings & Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

参数 Parameter	符号 Symbols	DB3		单位 Unit
		Min.	Max.	
最大功耗 Maximum Power Dissipation	P _D	150		mW
重复峰值导通电流 Repetitive peak on-state current t _p =20ms、f=120Hz	I _{TRM}	2		A
击穿电压 Breakover voltage (Note 1) C=22nF (Note 2)	V _{BO}	Min.	28	V
		Typ.	32	V
		Max.	36	V
击穿电压对称值 Breakover voltage symmetry C=22nF (Note 2)	V _{BO1} - V _{BO2}	Max.	3	V
动态回弹电压 Dynamic breakdown voltage (Note 1) V _{BO} and V _F at 10mA	ΔV	Min.	5	V
输出电压 Output voltage (Note 1)	V _O	Min.	5	V
击穿电流 Breakover current (Note 1)	C=22nF (Note 2)	Max	100	uA
上升时间 Rise time (Note 1)	See diagram 3	tr	Typ.	1.5
漏电流 Leakage current (Note 1)	V _R = 0.5 V _{BO} Max.	I _R	Max.	10
峰值电流 Peak current (Note 1)	See diagram 2	I _P	Min.	0.3
存储温度 Storage temperature rang	T _{STG}	-40 --- +125		°C
工作温度 Operating junction rang	T _J	-40 --- +125		°C

备注 Note:

- 1) 适用于正、反两极。 Applicable to both forward and reverse directions.
- 2) 与器件并联连接。 Connected in parallel to the device.

特性曲线 Characteristic Curves

图1. 电压-电流特性曲线

Diagram 1. Voltage - current characteristic curve.

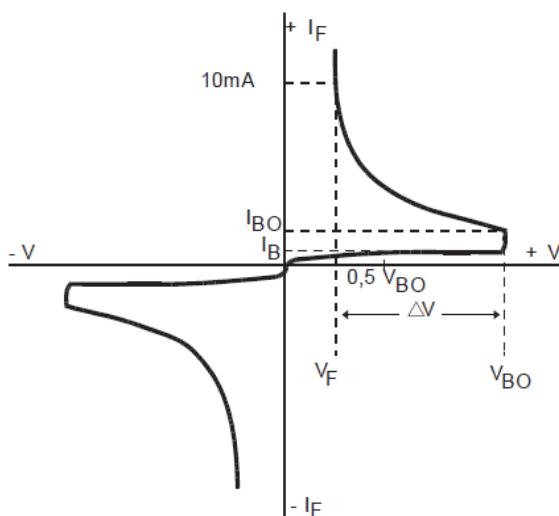


图2. 测试电路

Diagram 2: Test circuit.

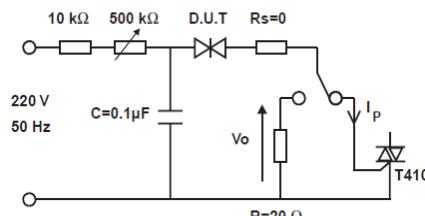


图3. 上升时间测量

Diagram 3: Rise time measurement.

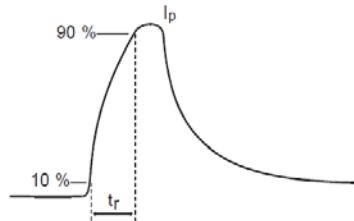


图4. 器件功耗降额曲线

Diagram 4: Power Dissipation Derating Curve.

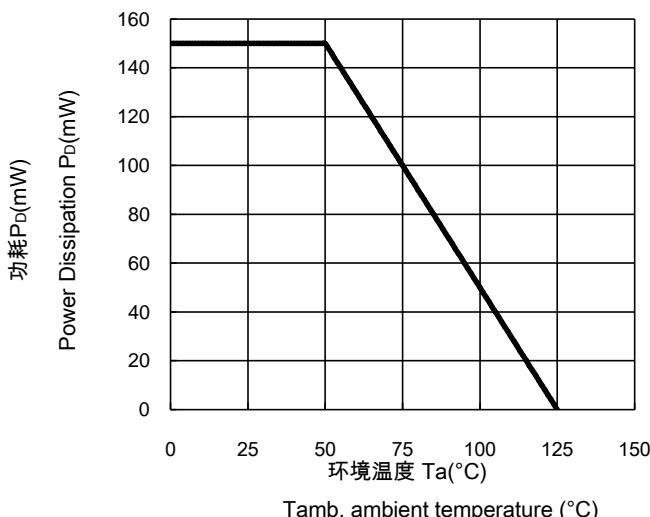


图5. 重复峰值导通电流 Vs 脉宽

Diagram 5: Repetitive peak on-state current Vs pulse width

